VS-6EWX06FNHM3

Vishay Semiconductors

Hyperfast Rectifier, 6 A FRED Pt®



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PRIMARY CHARACTERISTICS					
I _{F(AV)}	6 A				
V _R	600 V				
V _F at I _F	1.65 V				
t _{rr} (typ.)	14 ns				
T _J max.	175 °C				
Package	DPAK (TO-252AA)				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time, extremely low Q_{rr}
- 175 °C maximum operating junction temperature
- For PFC CCM operation
- Low forward voltage drop
- Low leakage current
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^\circ\mathrm{C}$
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		600	V
Average rectified forward current	I _{F(AV)}	T _C = 136 °C	6	
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \ ^{\circ}C$	50	А
Peak repetitive forward current	I _{FM}	$T_{C} = 136 \ ^{\circ}C, f = 20 \ \text{kHz}, d = 50 \ \%$	12	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	N	
Forward voltage		I _F = 6 A	-	2.50	3.1	V	
Forward voltage	V _F	I _F = 6 A, T _J = 150 °C	-	1.65	1.9		
		$V_{\rm R} = V_{\rm R}$ rated	-	-	20		
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA	
Junction capacitance	CT	V _R = 600 V	-	3.5	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time t _{rr}		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 10$	00 A/µs, V _R = 30 V	-	14	21		
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	16	-		
	۲r	T _J = 25 °C		-	19	-	ns A	
		T _J = 125 °C	I _F = 6 A dI _F /dt = 200 A/μs V _R = 390 V	-	27	-		
Peak recovery current I _{RRM}	1	$T_J = 25 \ ^{\circ}C$		-	3.0	-		
	IRRM	T _J = 125 °C		-	4.0	-		
Reverse recovery charge	Q _{rr}	$T_J = 25 \ ^{\circ}C$		-	28	-	nC	
		T _J = 125 °C		-	57	-		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	-	3	°C/W
Approximate weight				0.3		g
				0.01		oz.
Marking device		Case style DPAK (TO-252AA)		6EWX	D6FNH	



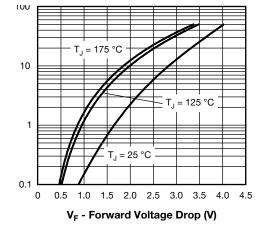
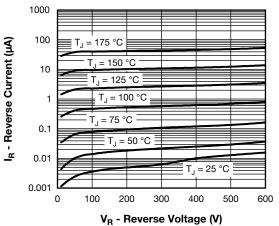
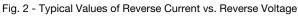
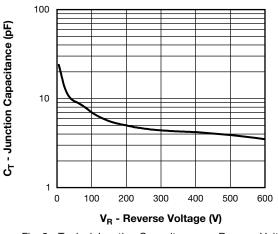


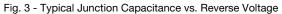
Fig. 1 - Typical Forward Voltage Drop Characteristics









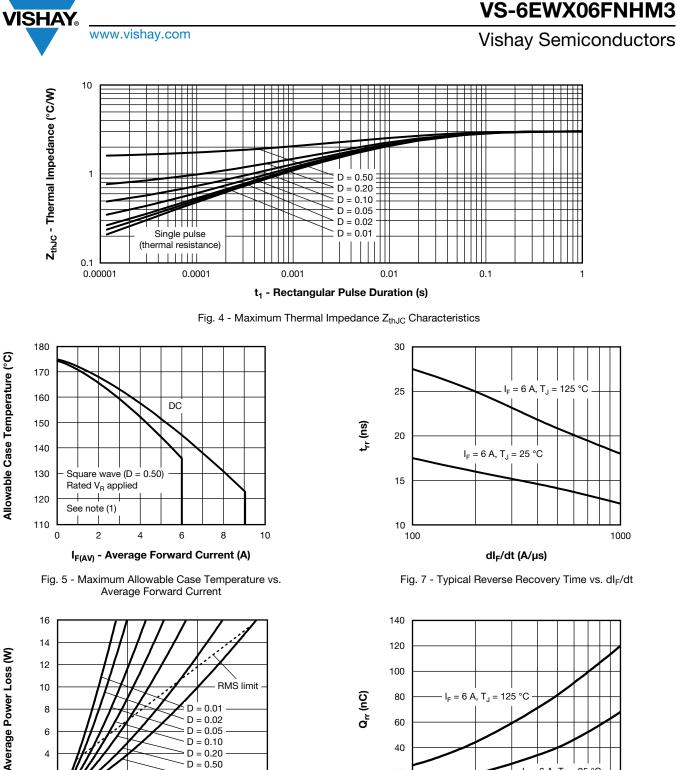


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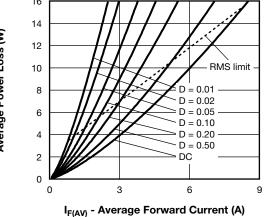


Fig. 6 - Forward Power Loss Characteristics

Note

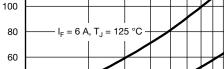
- (1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
 - Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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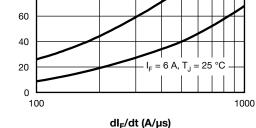


Fig. 8 - Typical Stored Charge vs. dl_F/dt





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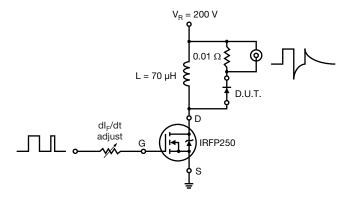
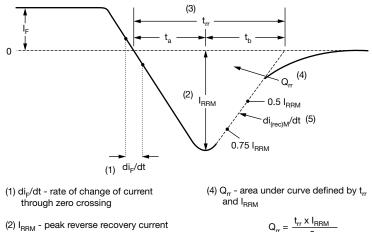


Fig. 9 - Reverse Recovery Parameter Test Circuit



⁽³⁾ t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

$$r = \frac{l_{rr} \times l_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

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Device code	vs-	6	Е	w	x	06	FN	TRL	н	М3
		2	3	4	5	6	7	8	9	10
	1 2 3	- Cur - Circ	hay Sen rent rati cuit conf	ng (6 = iguratior	6 A)	oduct				
	4	- Pao	single c kage id D-PAK	entifier:						
	5 6 7	- Vol	hyperfa tage rati = TO-25	ng (06 =	-					
	8	• T	one = tu R = tape RL = tap	e and ree		oriented	4)			
	9 10	• T - H = - Env	RR = tap AEC-Q vironmer = halog	pe and r 101 qua ntal digit	eel (righ alified :	it orient	ed)	terminat	tions lea	ad (Pb)-i

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-6EWX06FNHM3	75	3000	Antistatic plastic tube				
VS-6EWX06FNTRHM3	2000	2000	13" diameter reel				
VS-6EWX06FNTRRHM3	3000	3000	13" diameter reel				
VS-6EWX06FNTRLHM3	3000	3000	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95519				
Part marking information	www.vishay.com/doc?95518				
Packaging information	www.vishay.com/doc?95033				

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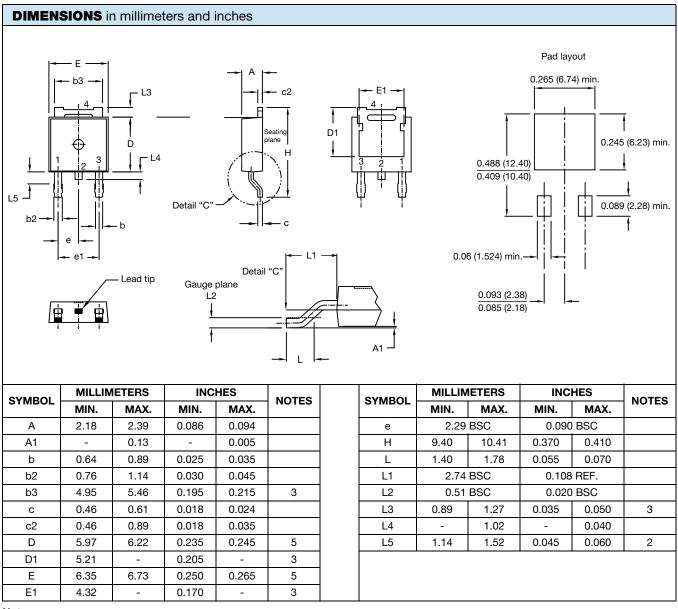


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Outline Dimensions

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DPAK (TO-252AA)



Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

⁽⁴⁾ Dimensions D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁵⁾ Outline conforms to JEDEC[®] outline TO-252AA



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